

Combination of Scanning Probe Microscope and X-rays for Detection of Electrons

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FP6-STREP



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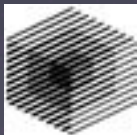
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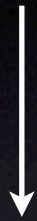
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Scientific Cases

Nano system



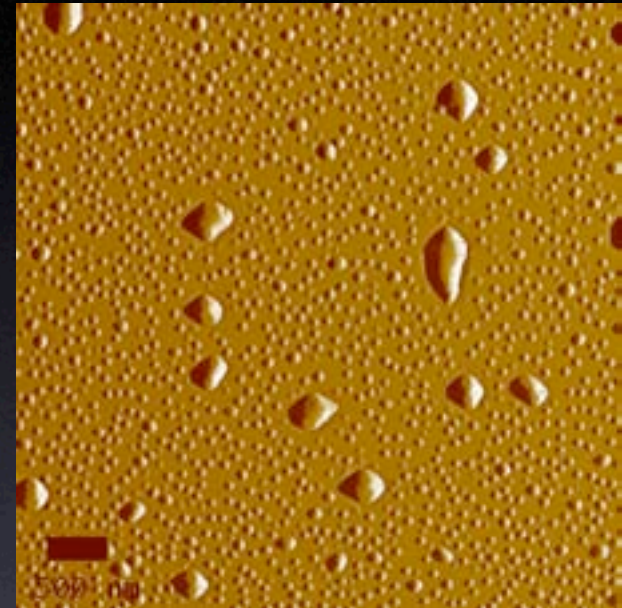
Topological information



Chemical information
Electronic information

Force interaction
Nano-manipulation

X-rays needed



Tip surface distance control

Tuning Forks:

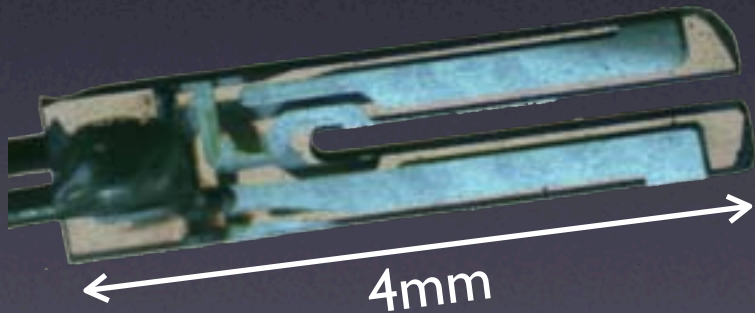
Piezo-electric

Q Higher than 10 000 without any tip

Allow very small amplitudes $< 1\text{nm}$

No laser

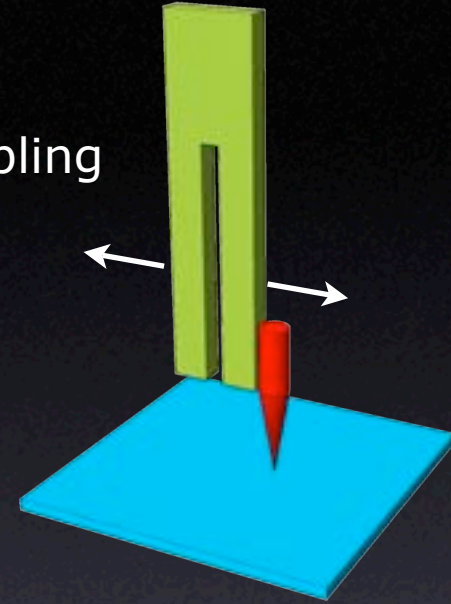
A tip must be glued



Distance regulation:
frequency shift - PLL regulation+PID

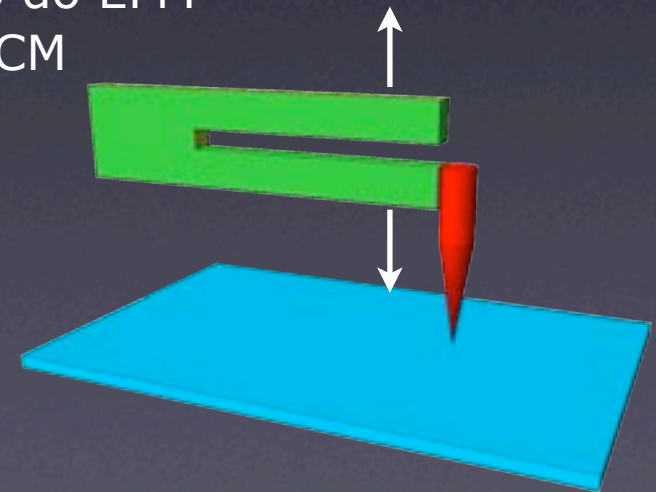
a. Parallel

- Weak capacitive coupling
- Possibility to do SCM
- No possibility of EFM



b. Perpendicular

- Good capacitive coupling
- Possibility to do EFM
- As well as SCM



Setup

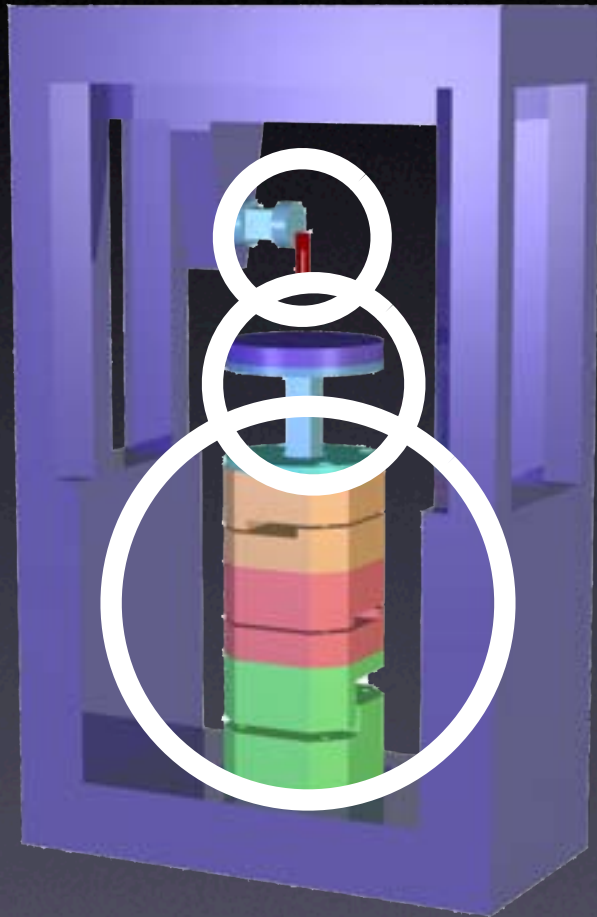


X-ray
Beam

Fluorescence
Detector



Microscope

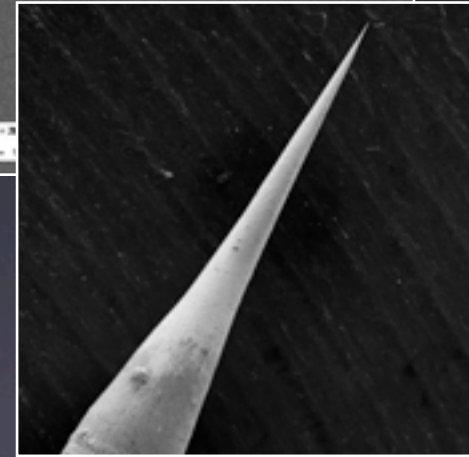
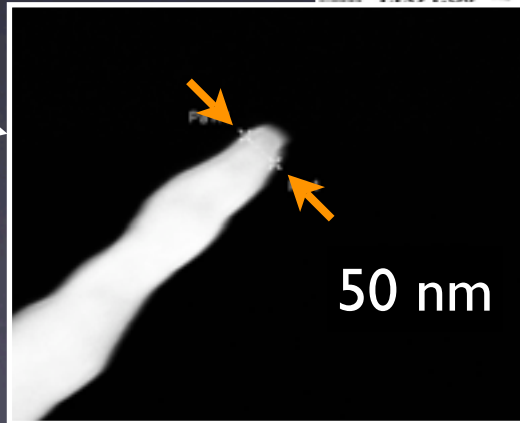
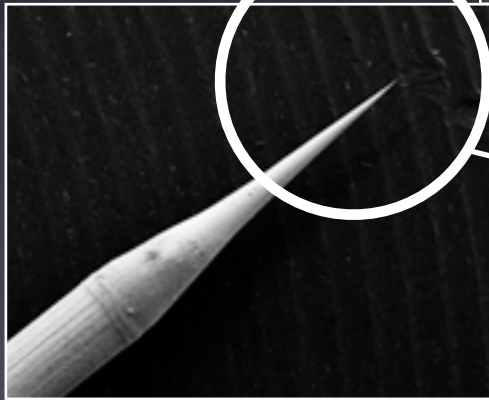
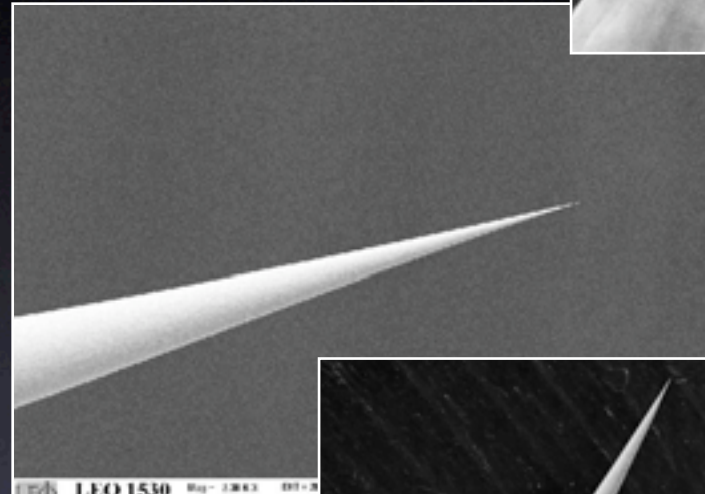
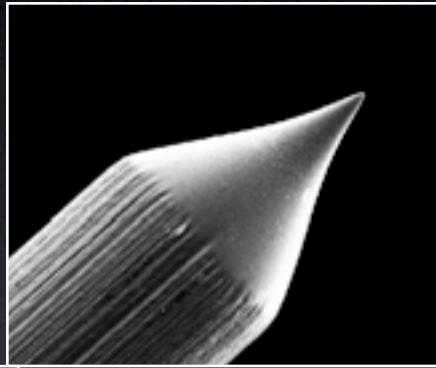
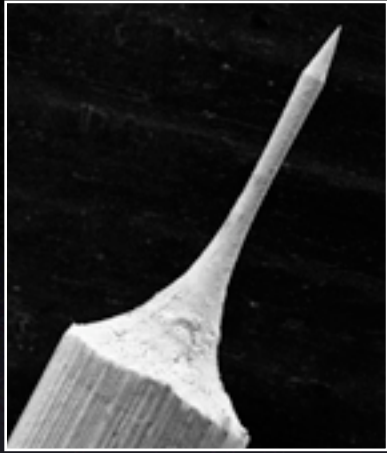


Tuning Forks system

XYZ direction fine movement
(Travel: $9\mu\text{m}$, Res: 0.02nm)

XYZ direction coarse approach
Attocube Systems
(Travel: 4mm , Res: 25nm)

Metallic Tips

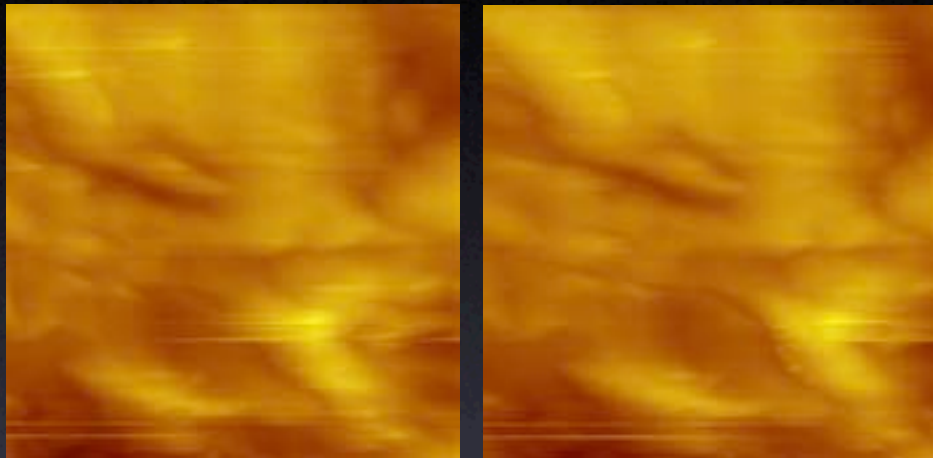


NaOH chemical etched

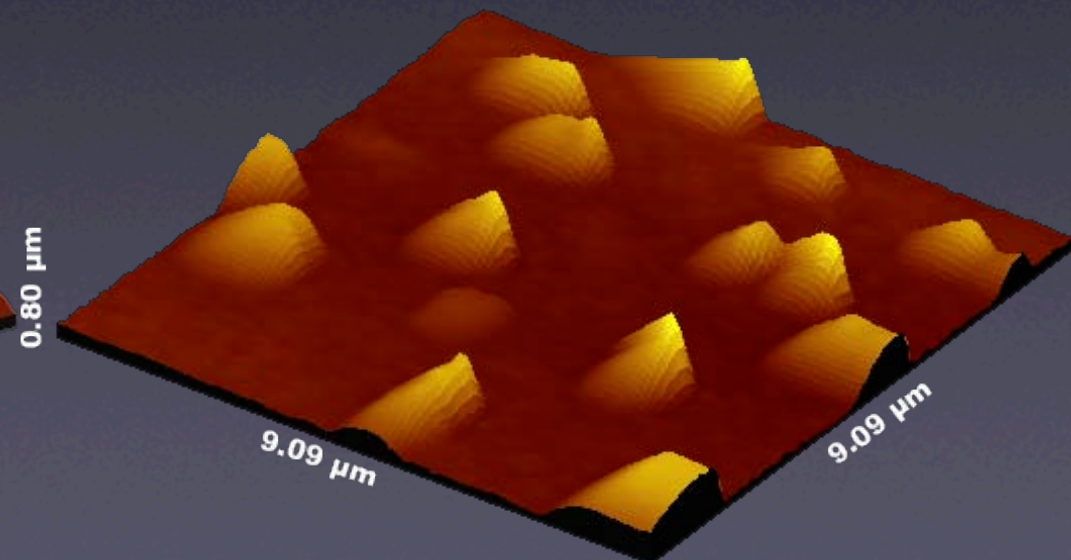
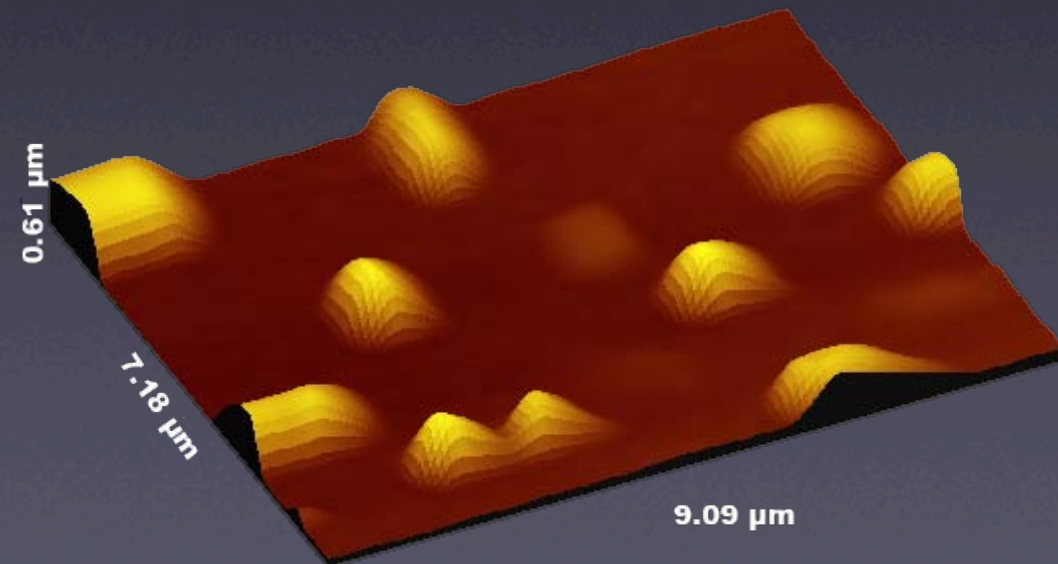
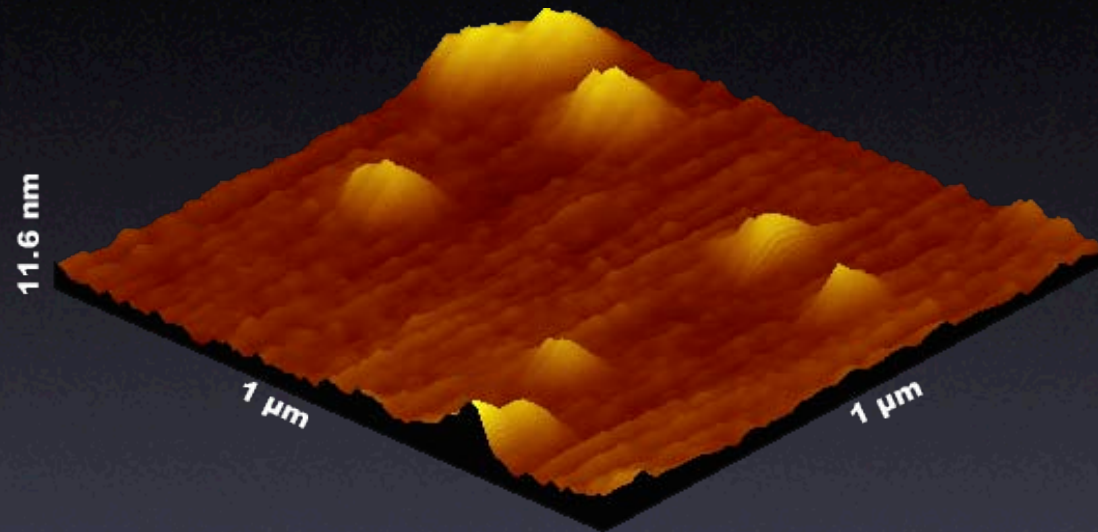
Curvature radius: 10-100nm

Images Capabilities

STM Images



AFM Images



Experiment I

Goal:

Photoelectron detection.
Detection chain validation.
Simulation - experience comparison

Method:

Faraday cup design.
Lock-in detection.

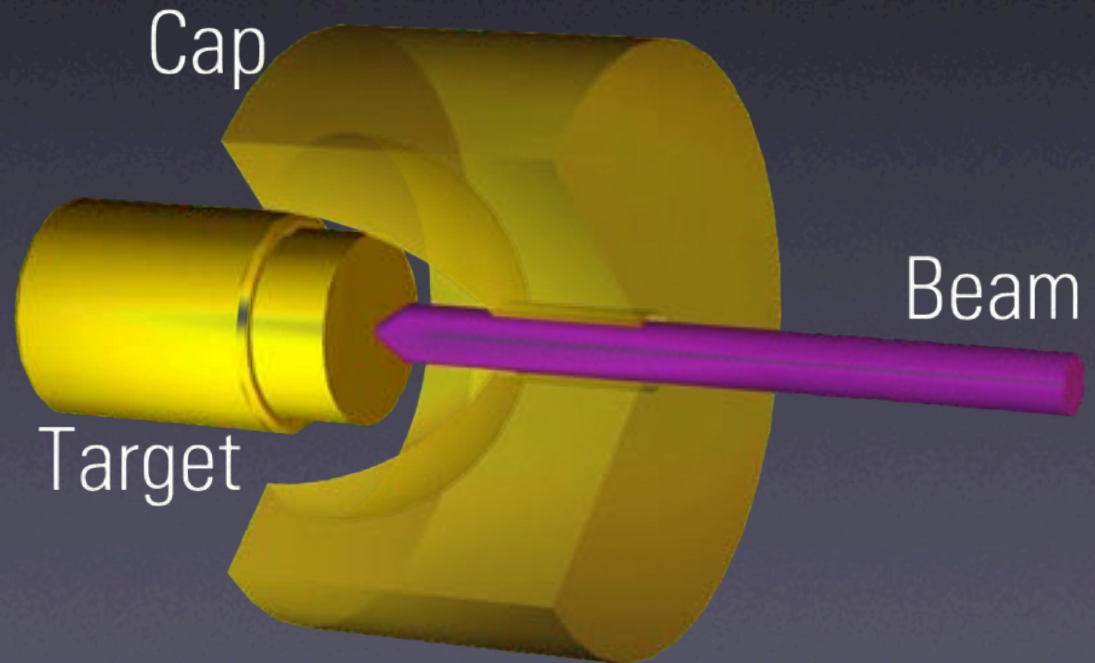
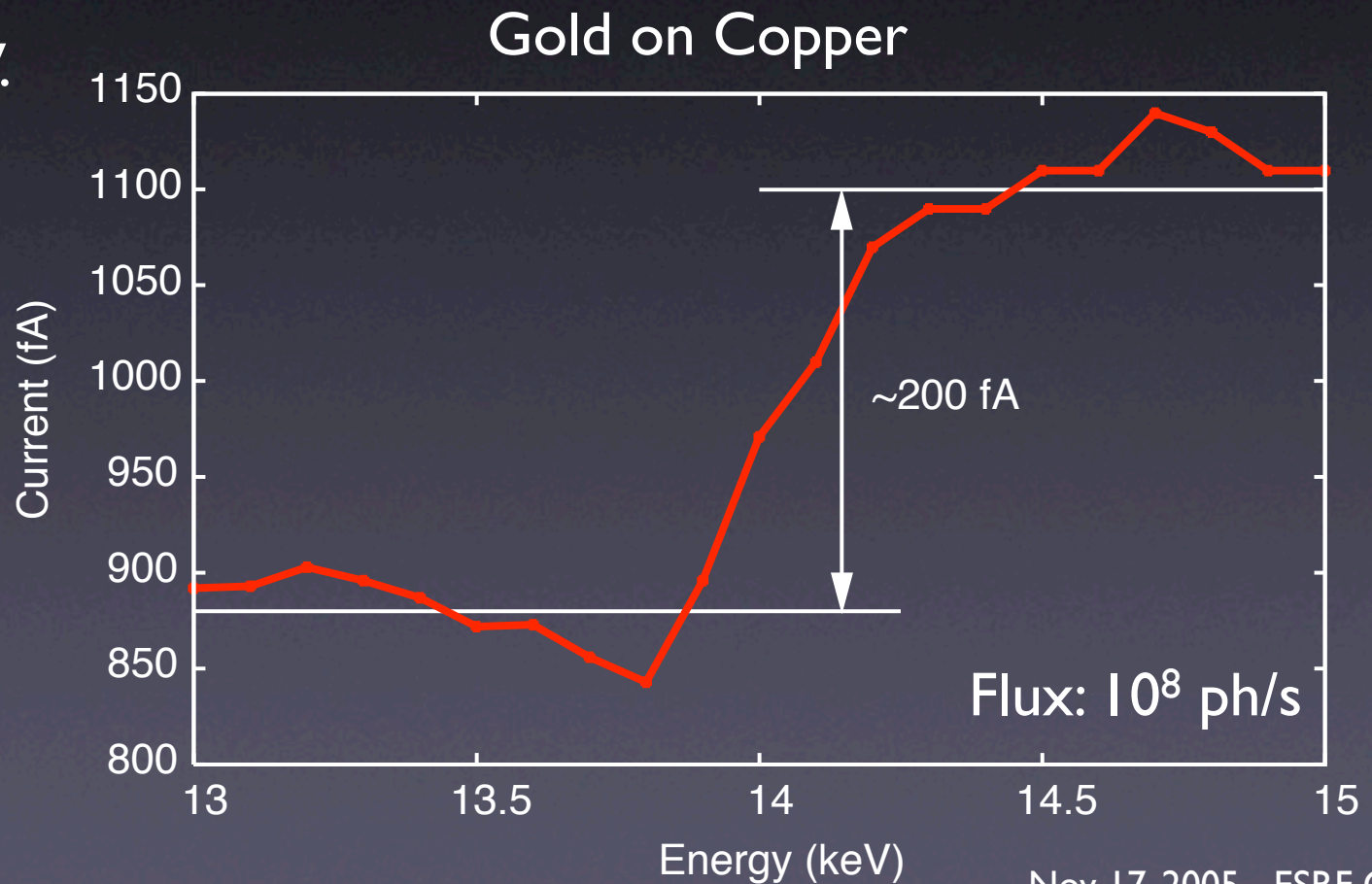


Photo-Electron Yield simulation

- Monte Carlo codes: EGS4 and Penelope
- Limitation: do not follow the slow electrons
- EGS4 > 1 keV
- Penelope > 100 eV.



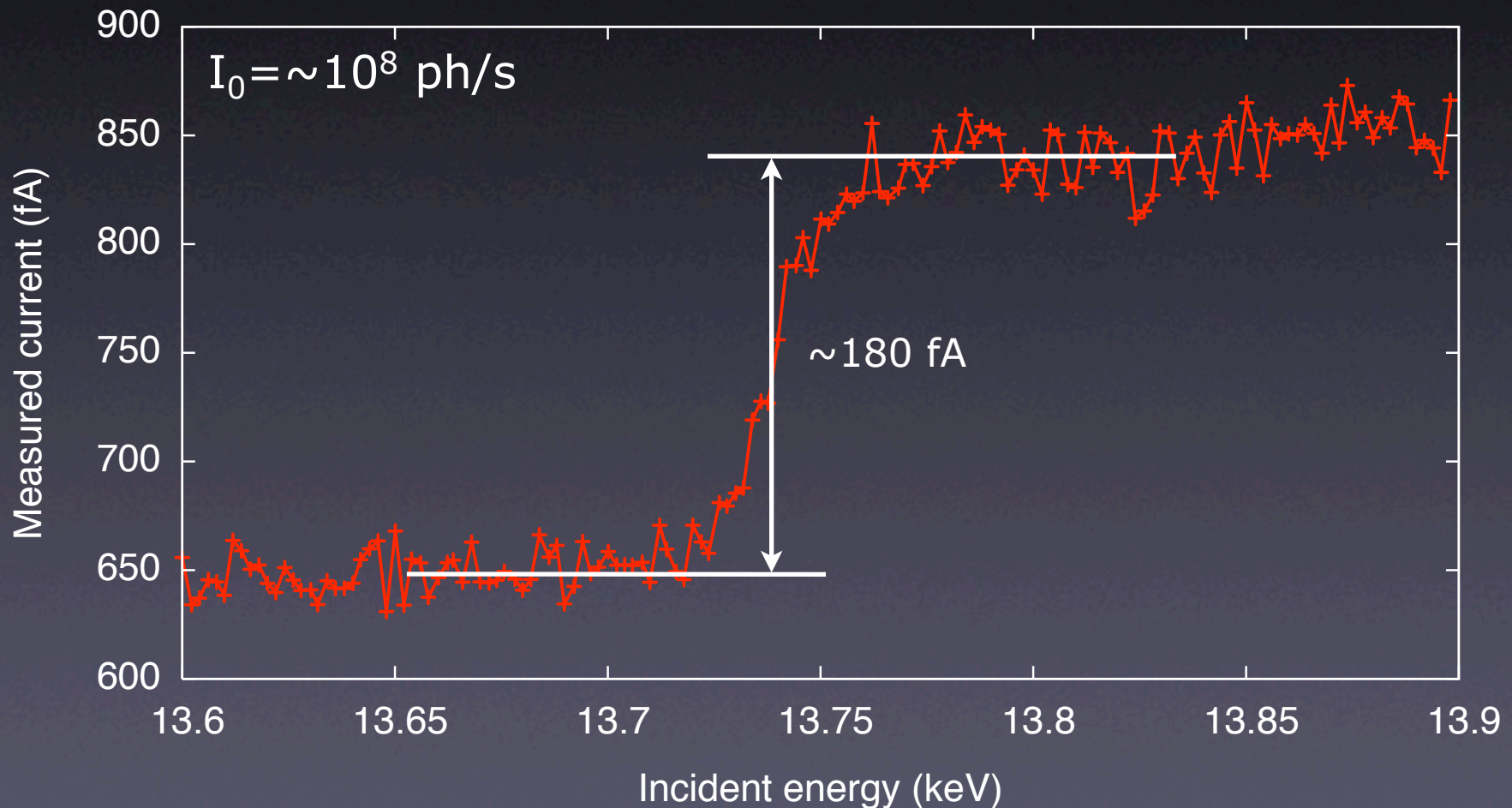
Experiment Results

Experiment parameters:

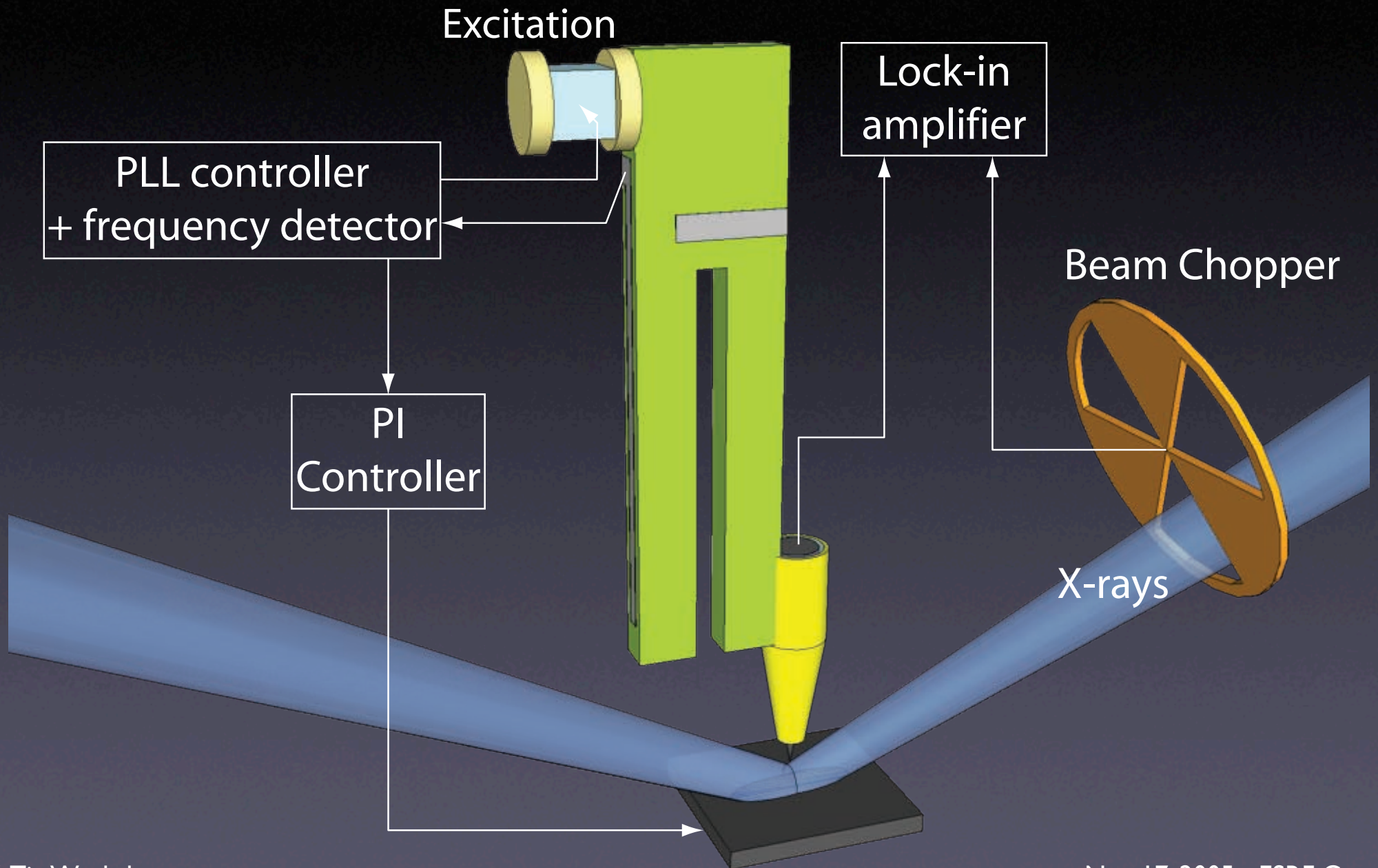
Monochromatic Beam ($1 \times 3 \mu\text{m}$)

BM05 - $I_0 = 10^8 \text{ ph/s}$ - $E = 13.7 \text{ keV}$ (L_2 edge of Au)

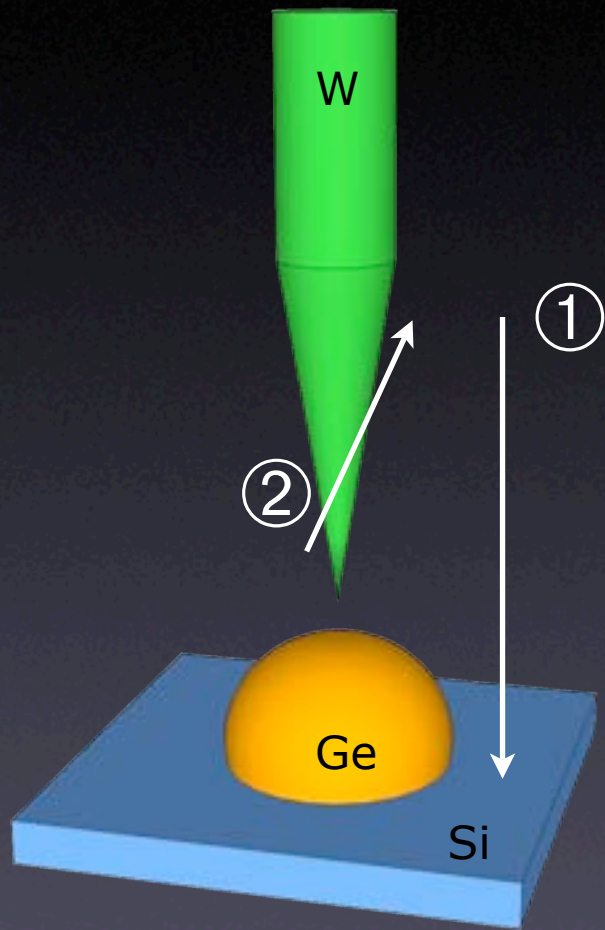
Gold layer on Copper - L_2 Au Edge



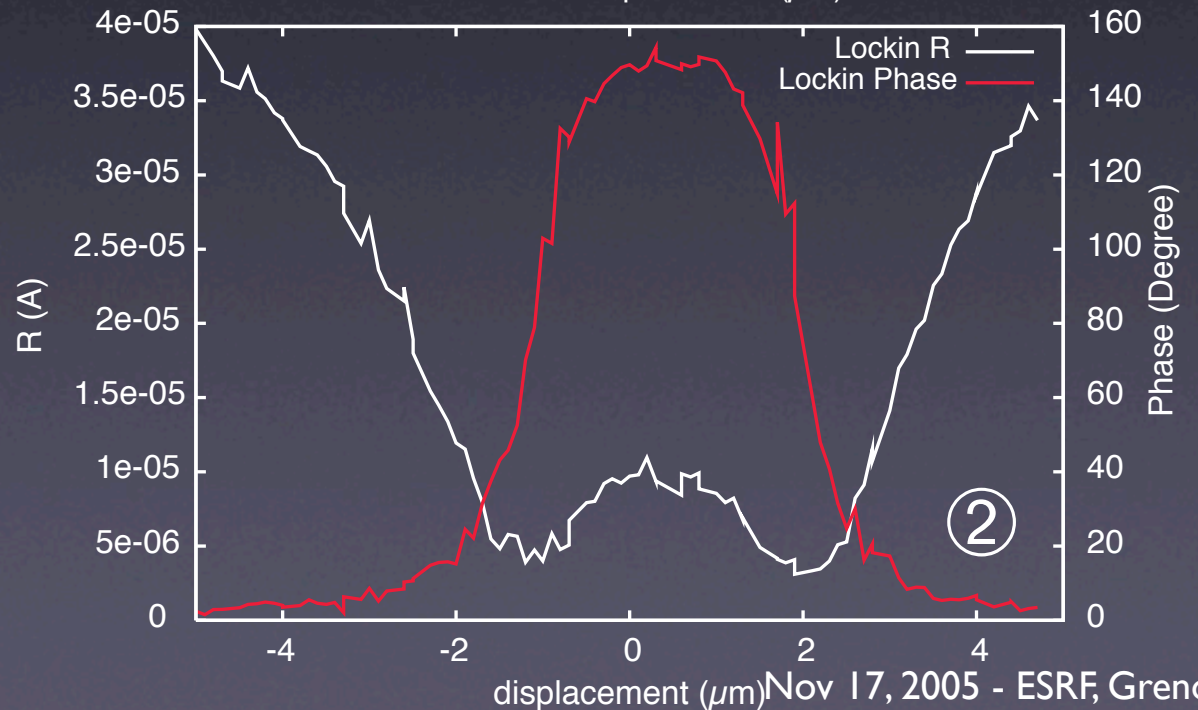
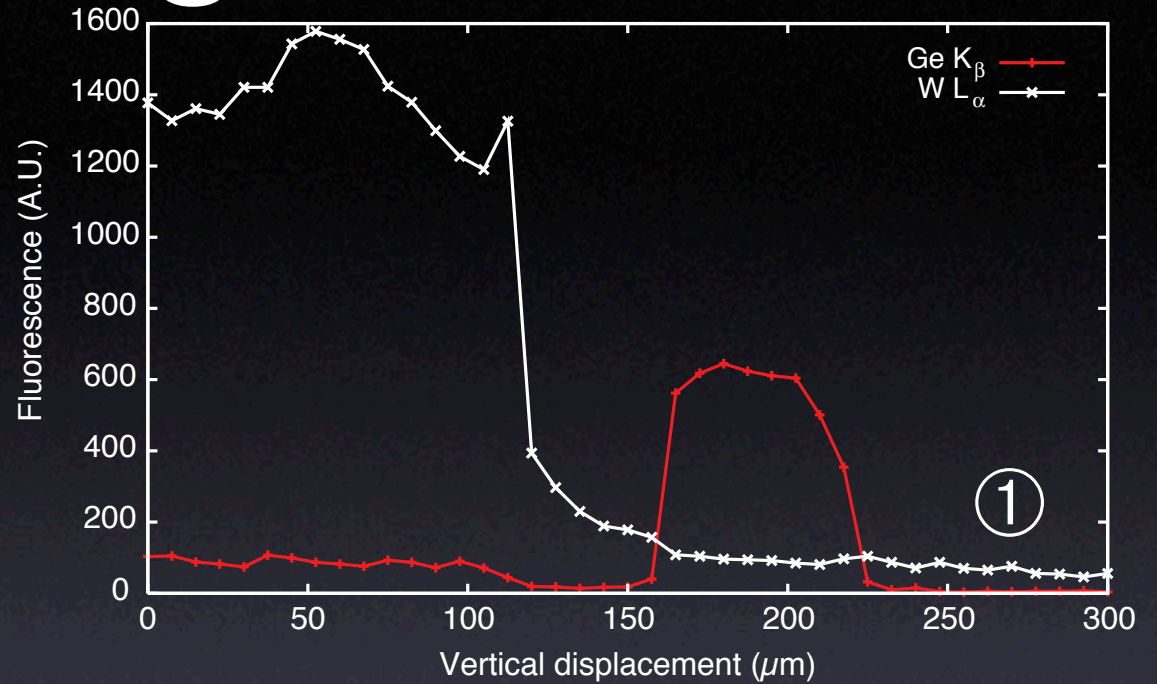
Experiment II



Tip Alignment



Ge K_{β} : 9.88 keV W L_{α} : 8.39 keV



Experiment Parameters

Setup:

ID22 Beamline ESRF

Focusing device: Kirk-Patrick Baez.

Ge dots on Si

Beam characteristic:

Monochromatic Beam

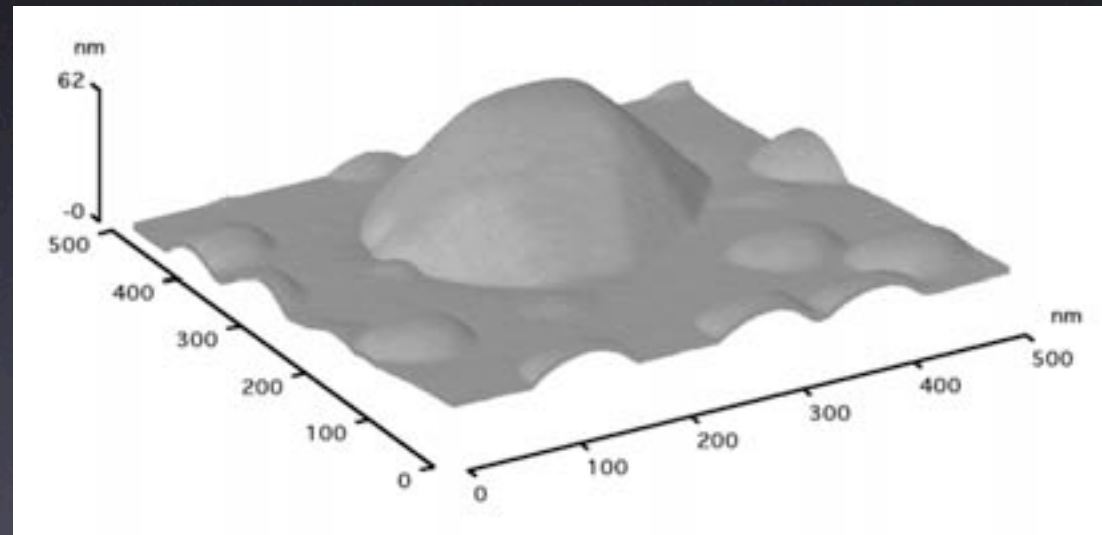
Size: $2 \times 3 \mu\text{m}^2$

Incidence angle: $\sim 5^\circ$

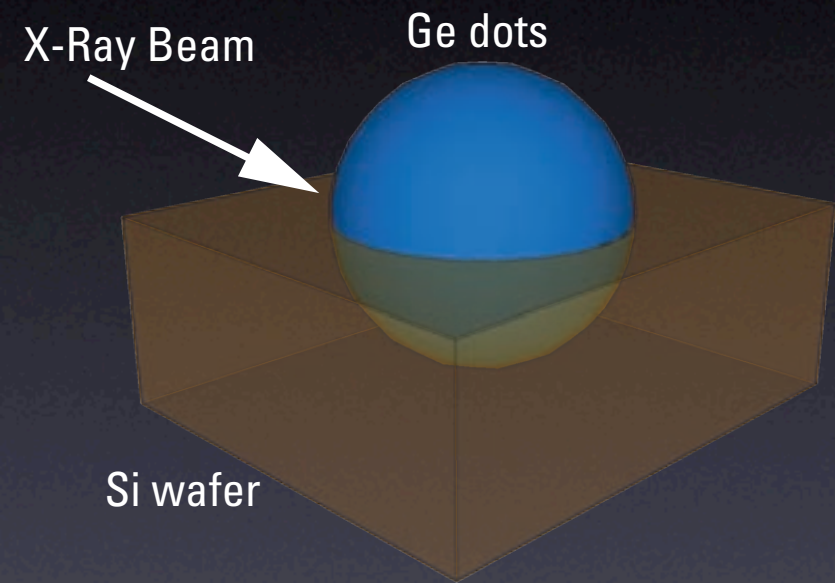
$I_0 = 6 \cdot 10^{11}$ ph/s

$E = 11.1$ keV (K edge of Ge)

Sample-Tip distance: ~ 10 nm

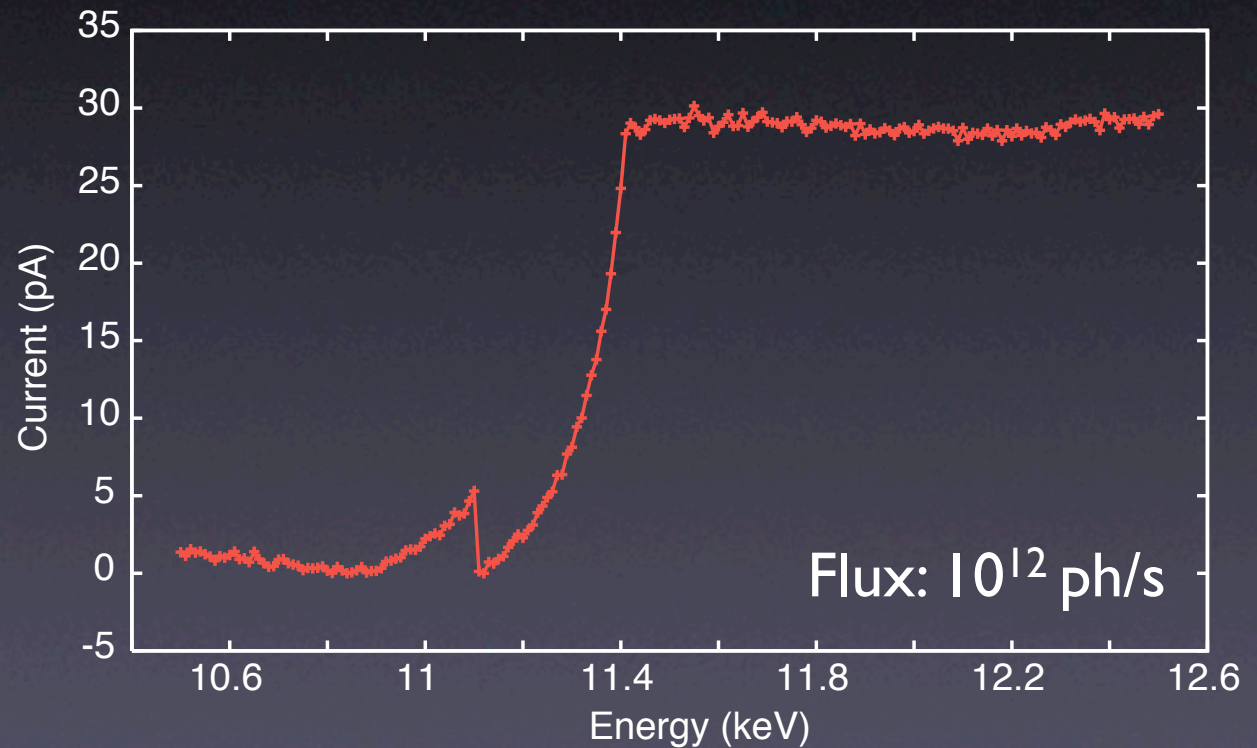


Simulation

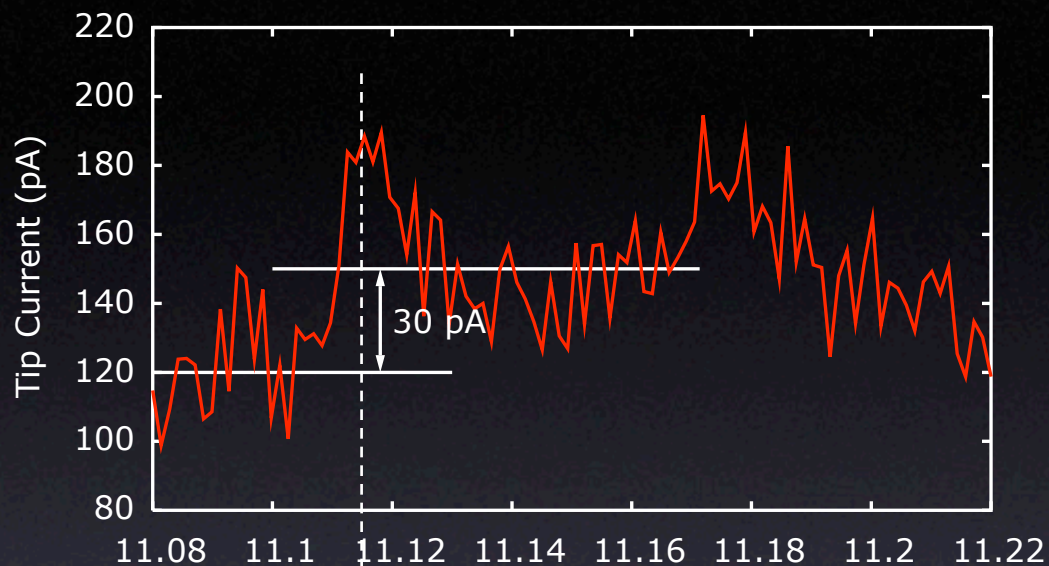


Ge dot $R=36\text{nm}$
Si layer $l=10\mu\text{m}$

Ge Dot on Si wafer
Code: EGS4



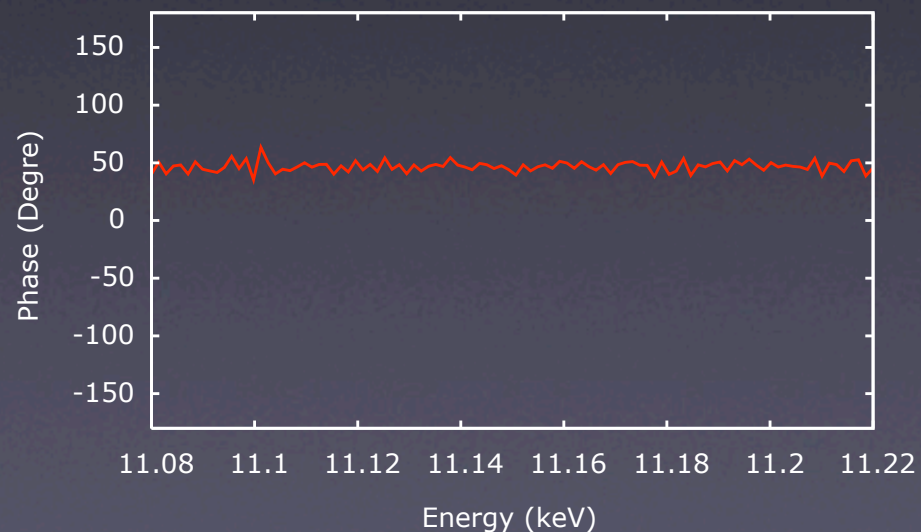
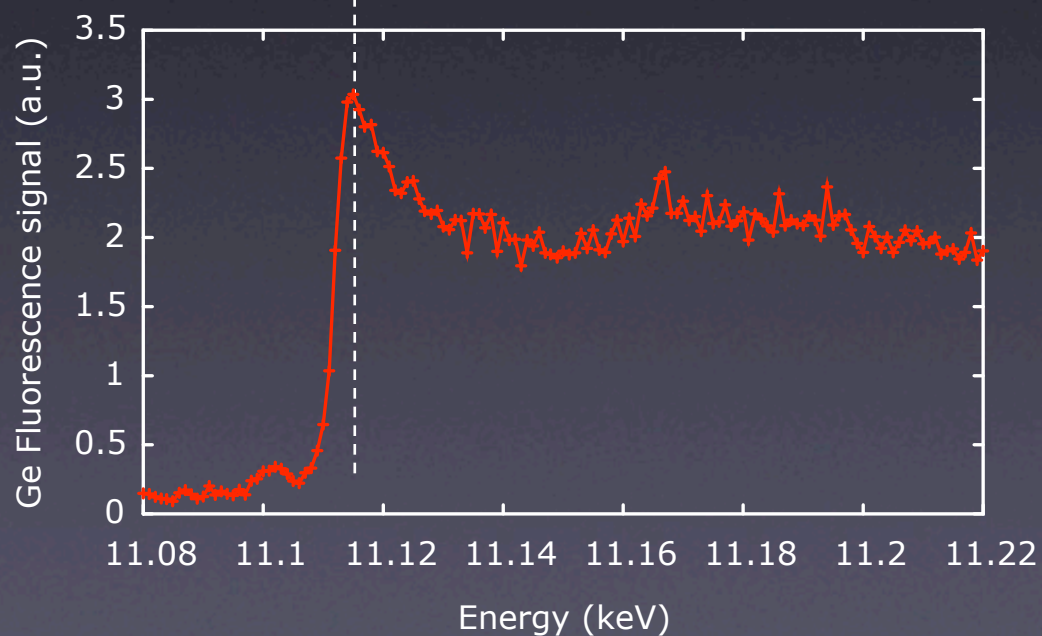
XANES



Simulation with EGS4 for
Ge dots on Si: $I_{\text{jump}}=28\text{pA}$

AFM (sample/tip) regulation:
10 nm during the measure

Noise Level: few fA

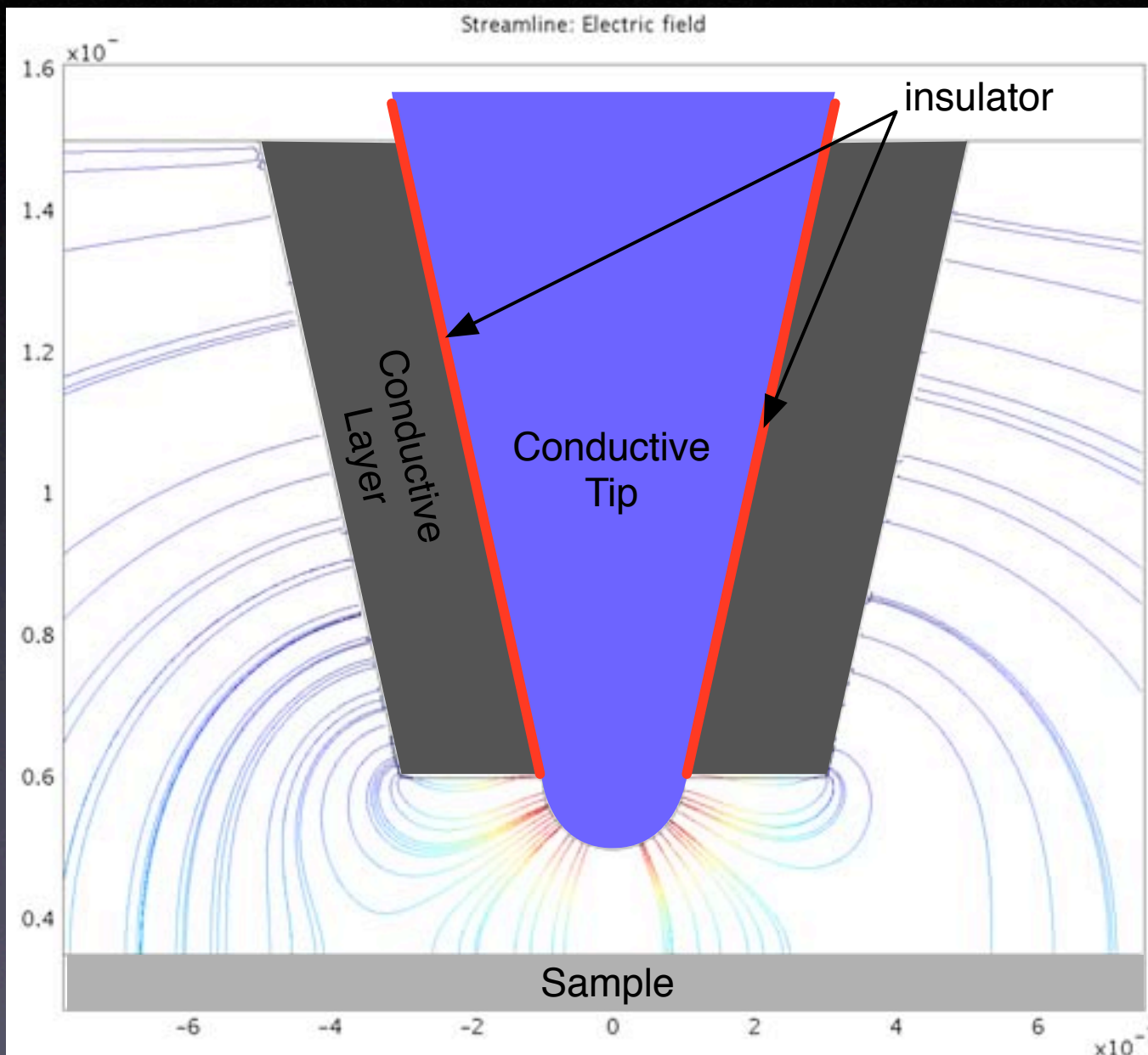


Conclusion

- 📌 A home built microscope compatible with X-rays synchrotron instrumentation.
- 📌 AFM-STM Imaging Capabilities
- 📌 We shows sensitivity to photo-excited electrons.

What Next

Coaxial Tips Why ?



Coaxial Tips development



Tungsten Wire (250 μm),
Chemical Etched.

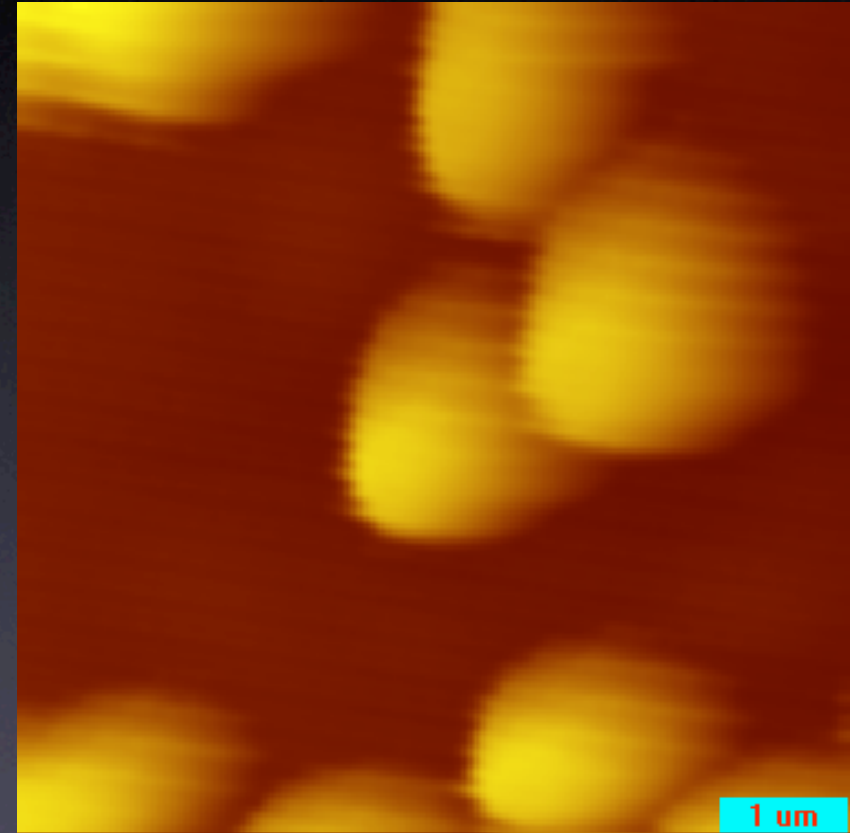
Parylene film ($\sim 1000\text{\AA}$)

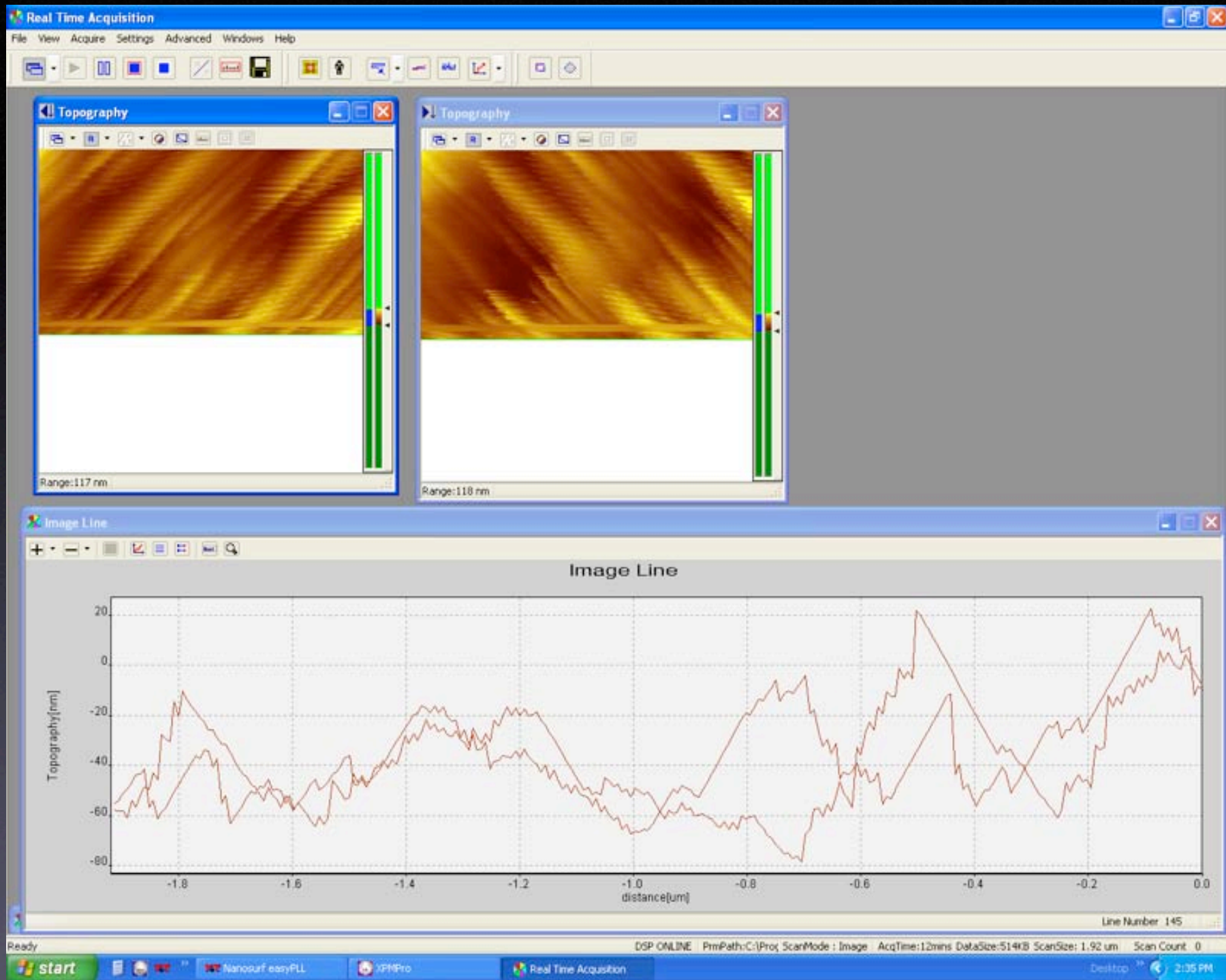
Gold layer ($\sim 1000\text{\AA}$)

End opening (FIB)

Other development

- Implementation on beamline
 - Imaging capability.
 - Resolution: 50 nm.
- Noise problem:
 - Mechanical noise (Pump, ...)
 - Electronic Noise.
- Collaboration with ID I





Acknowledgment

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